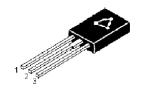
PNP Transistor T0-126







Pin Configuration:

- 1. Emitter
- 2. Collector
- 3. Base

Feature:

- · PNP Plastic Power Transistors
- · Medium Power Linear and Switching Applications

Absolute Maximum Ratings

Description	Symbol	-	BD138	Unit
Collector-Base Voltage (Open Emitter)	V _{CBO}		60	V
Collector Emitter Voltage (Open Base)	V _{CEO}		60	V
Collector Current	I _C		1.5	А
Total Power Dissipation upto T _C = 25°C	P _{tot}	Max.	12.5	W
Junction Temperature	T _j		150	°C
Collector-Emitter Saturation Voltage I _C = 0.5A, I _B = 0.05A	V _{CE (Sat)}		0.5	V
DC Current Gain I _C = 0.15A; V _{CE} = 2V	h _{FE}	Min. Max.	40 250	-

Ratings (at $T_a = 25$ °C unless otherwise specified)

Description	Symbol	-	BD138	Unit
Collector-Base Voltage (Open Emitter)	V_{CBO}		60	V
Collector Emitter Voltage (Open Base)	V_{CEO}		0	
Emitter-Base Voltage (Open Collector)	V _{EBO}		5	
Collector Current	I _C	Max.	1.5	۸
Base Current	I _B		0.5	A
Total Power Dissipation up to T _A = 25°C Derate above 25°C	P _{tot}		1.25 10	W mW/°C

www.element14.com www.farnell.com www.newark.com



PNP Transistor T0-126



Ratings (at $T_a = 25$ °C unless otherwise specified)

Description	Symbol	-	BD138	Unit
Total Power Dissipation up to T _C = 25°C Derate above 25°C	P_{tot}	Max.	12.5 100	W mW/°C
Junction Temperature	T _j		150	°C
Storage Temperature	T _{stg}	-	-65 to +150	

Thermal Resistance

From Junction to Case	R _{th (j-c)}	-	10	°C/W
From Junction to Ambient	R _{th (j-a)}	-	100	C/VV

Characteristics ($T_a = 25$ °C unless otherwise specified)

Description	Symbol	-	BD138	Unit
Collector Cut off Current $I_E = 0$; $V_{CB} = 30V$ $I_E = 0$; $V_{CB} = 30V$; $T_C = 125$ °C	I _{СВО}	Max.	0.1 10	μА
Emitter Cut off Current I _C = 0; V _{EB} = 5V	I _{EBO}		10	
Breakdown Voltages $I_C = 0.03A$; $I_B = 0$ $I_C = 1mA$; $I_E = 0$ $I_E = 1mA$; $I_C = 0$	V _{CEO (Sus)} * V _{CBO} V _{EBO}	Min.	60 60 5	V
Saturation Voltage $I_C = 0.5A$; $I_B = 0.05A$	V _{CE (sat)} *	Max.	0.5	V
Base-Emitter On Voltage $I_C = 0.5A$; $V_{CE} = 2V$	V _{BE (on)} *	ividă.	1	
DC Current Gain I _C = 0.15A; V _{CE} = 2V**	h _{FE} *	Min. Max.	40 250	-

** hFE Classification:

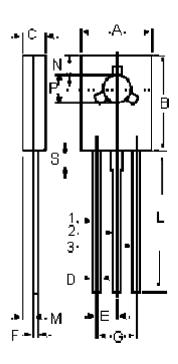
40 Min. Max. 100 -10 Min. 63 Max. 160 -16 Min. 100 Max. 250 -25 Min. 160 Max. 400



^{*} Pulse Test: Pulse Width = ≤300µs, Duty Cycle ≤2%.

PNP Transistor TO-126





Dimensions	Min.	Max.	
А	7.4	7.8	
В	10.5	10.8	
С	2.4	2.7	
D	0.7	0.9	
E	2.25 (Typical)		
F	0.49	0.75	
G	4.5 (Typical)		
L	15.7 (Typical)		
М	1.27 (Typical)		
N	3.75 (Typical)		
Р	3	3.2	
S	2.5 (Typical)		

Dimensions: Millimetres

Pin Configuration:

- 1. Emitter
- 2. Collector
- 3. Base

Part Number Table

Description	Part Number	
Transistor, PNP, TO-126	BD138	

Important Notice: This data sheet and its contents (the "Information") belong to the members of the Premier Farnell group of companies (the "Group") or are licensed to it. No licence is granted for the use of it other than for information purposes in connection with the products to which it relates. No licence of any intellectual property rights is granted. The Information is subject to change without notice and replaces all data sheets previously supplied. The Information supplied is believed to be accurate but the Group assumes no responsibility for its accuracy or completeness, any error in or omission from it or for any use made of it. Users of this data sheet should check for themselves the Information and the suitability of the products for their purpose and not make any assumptions based on information included or omitted. Liability for loss or damage resulting from any reliance on the Information or use of it (including liability resulting from negligence or where the Group was aware of the possibility of such loss or damage arising) is excluded. This will not operate to limit or restrict the Group's liability for death or personal injury resulting from its negligence. Multicomp is the registered trademark of the Group. © Premier Farnell plc 2012.

www.element14.com www.farnell.com www.newark.com

